

# IRF730

N-channel mosfet transistor

## ◆ Features

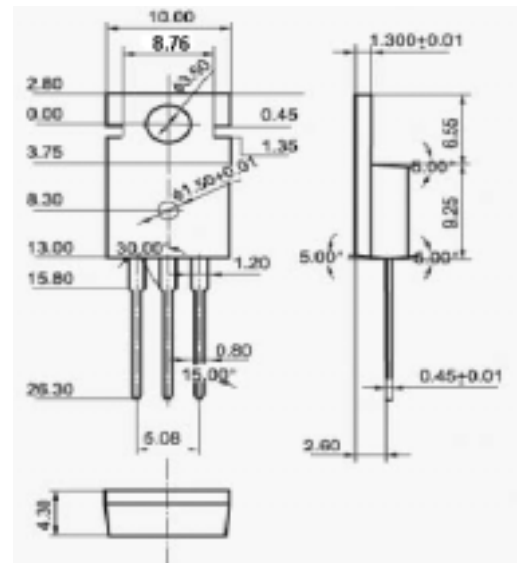
- With TO-220 package
- Simple drive requirements
- Fast switching
- $V_{DSS}=400V$ ;  $R_{DS(ON)} 1.0 \Omega$ ;  $I_D=5.5A$
- 1.gate 2.drain 3.source

## ◆ Absolute Maximum Ratings $T_c=25$

SYMBOL	PARAMETER	RATING	UNIT
$V_{DSS}$	Drain-source voltage ( $V_{GS}=0$ )	400	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $T_c=25$	5.5	A
$P_{tot}$	Total Dissipation@ $T_c=25$	74	W
$T_j$	Max. Operating Junction temperature	150	
$T_{stg}$	Storage temperature	-65~150	



1 2 3



TO-220

## ◆ Electrical Characteristics $T_c=25$

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS}=0$ ; $I_D=0.25mA$	400		V
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}$ ; $I_D=0.25mA$	2	4	V
$R_{DS(ON)}$	Drain-source on-stage resistance	$V_{GS}=10V$ ; $I_D=3.3A$		1.0	
$I_{GSS}$	Gate source leakage current	$V_{GS}=\pm 20V$ ; $V_{DS}=0$		$\pm 100$	nA
$I_{DSS}$	Zero gate voltage drain current	$V_{DS}=400V$ ; $V_{GS}=0$		25	$\mu A$
$V_{SD}$	Diode forward voltage	$I_F=5.5A$ ; $V_{GS}=0$		1.6	V